Express Mail No.: <u>EV 371 773 148 US</u>

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

pplication of: Wai Mun Lee

Confirmation No.:

9136

Serial No.:

10/630,300

Art Unit:

1751

Filed:

July 30, 2003

Examiner:

To be assigned

For:

Cleaning Compositions and Methods of

Attorney Docket No.: 60937-194-US

Use Thereof

(formerly 8317-194-999)

TRANSMITTAL OF POWER OF ATTORNEY BY ASSIGNEE REVOKING PREVIOUS POWERS OF RECORD

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Applicants' attorney encloses herewith a Revocation and Power of Attorney by Assignee for the above identified patent application.

Please change the attorney docket number to 60937-194-US. Future correspondence should be forwarded to James S. McDonald, customer no. 24341.

No fee is believed due at this time, however, the Commissioner is authorized to charge any fees associated with this communication to Morgan, Lewis & Bockius LLP Deposit Account No. 50-0310 (Order No. 60937-194-US). A copy of this sheet is enclosed for such purpose.

Respectfully submitted,

Date March 12, 2004

MORGAN, LEWIS & BOCKIUS LLP

3300 Hillview Avenue Palo Alto, CA 94304

(650) 493-4935

P F COLLINA TO THE PART & TRUSTERS

REVOCATION AND POWER OF ATTORNEY

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

SIR:

EKC Technology, Inc., owner of the entire right, title and interest in, to and under the inventions described and claimed in the patent applications identified in the attached Schedule A, hereby revokes all previous powers of attorney and appoints Morgan, Lewis & Bockius LLP, customer no. 24341, and each of them, its attorneys, to prosecute each of these patent applications, and to transact all business in the Patent and Trademark Office connected therewith.

Please direct all future correspondence to Customer Number 24341, Morgan, Lewis & Bockius LLP, located at 3300 Hillview Avenue, Palo Alto, California 94304, and direct all telephone calls to Morgan, Lewis & Bockius LLP at (650) 493-4935.

Assignee:

EKC Technology, Inc.

Data

7 Feb 2004

Signature:

Michael A. Fury

Typed Name: Position/Title:

Vice President, R&D and Engineering

Address:

2520 Barrington Court Hayward, CA 94545

	MAR 1 2 2004	Schedule A			
App #	TOTA TRADE	linventor(s):	Filling Date	Maw Allomay: Docket No.*	Tormer/Allome Docker No.
· Whhansy]	Compositions for Cleaning Organic		ALL THE RESIDENCE OF THE PARTY		
	and Plasma Etched Residues for				
09/903,064	Semiconductor Devices	Small, et al.	07/10/2001	60937-091-US	8317-091-999
	Method of and Apparatus for				
09/874,330	Substrate Pre-Treatment	Maloney, et al.	06/06/2001	60937-111-US	8317-111-999
	Chemical Mechanical Polishing				
09/985,870	Compositions	Small, et al.	11/06/2001	60937-114-US	8317-114-999
	Oxalic Acid as a Semiaqueous				
	Cleaning Product for Copper and		04/04/0002	60027 446 116	9217 116 000
10/421,706	Dielectrics	Lee, et al.	04/24/2003	60937-116-US	8317-116-999
40/400 405	Sulfoxide Pyrolid(in)one Alkanolamine	Zhou, et al.	07/12/2002	60937-118-US	8317-118-999
10/193,185	Cleaner Composition	Zilou, et al.	01/12/2002	00937-110-03	0317-110-993
	Method for the Deposition of Materials				
09/876,944	from Mesomorphous Films	Vasquez, et al.	06/08/2001	60937-120-US	8317-120-999
33/010,344	Post Etch Cleaning Composition for	vaoquoz, or an			
10/007,134	Dual Damascene System	Payne, et al.	12/04/2001	60937-123-US	8317-123-999
10,007,101	Photolytic Conversion Process to				
10/263,701	Form Patterned Amorphous Film	Bravo-Vasquez, et al.	10/04/2002	60937-126-US	8317-126-999
	Cleaning Solutions Including				
	Nucleophilic Amine Compound				
	Having Reduction and Oxidation				
09/988,545	Potential	Lee, et al.	11/20/2001	60937-127-US	8317-127-999
	Method and Compositions for				
	Chemically Treating A Substrate				
10/060,109	Using Foam Technology	Patel, et al.	01/28/2002	60937-129-US	8317-129-999
	Cleaning Solution Including	٠,.			
	Nucleophilic Amine Compound			·	
40405.005	Having Reduction and Oxidation	l so stal	05/01/2002	60937-135-US	8317-135-999
10/135,695	Potential	Lee, et al.	05/01/2002	60937-135-US	8317-137-999
10/448,127	Fluoride Layer and Removing Same	Melvin K. Carter	05/30/2003	00937-137-03	0317-137-998
	Process for the Use of Bis-Choline				
	and Tris-Choline in the Cleaning of				
401000 055	Quartz-Coated Polysilicon and Other	Charm et al	10/22/2003	60937-139-US	8317-139-999
10/689,657	Materials Classics Compositions Containing	Charm, et al.	.10/22/2003	00937-139-03	6317-139-99
	Cleaning Compositions Containing				
	Hydroxylamine Derivatives and Process Using Same for Residue				
10/680 620	Removal	Zhou, et al.	10/22/2003	60937-140-US	8317-140-999
10/689,620	Nemoval	Zilou, et al.	10/22/2000	30007 170 00	301. 110 00.
	Composition for Exfoliation Agent to			1	
10/689,616	be Used to Remove Resist Residues	Melvin K. Carter	10/22/2003	60937-141-US	8317-141-999
. 5, 555, 510	Padusing Oxida Loss When Using				

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05/02/2003

Lee, et al.

Reducing Oxide Loss When Using Fluoride Chemistries to Remove Post-Etch Residues in Semiconductor

Processing

60/467,131

	Market and the state of the sta		Filing	New Attorney	Former Attorney
Ápp #	Title	inventor(s)	Date	1,000	Docket No.
	Method for Depositing Patterned		07/00/0000	00007 440 440	0047 440 000
10/630,301	Films of Materials	Hill, et al.	07/30/2003	60937-143-US	8317-143-999
	Methods for the Deposition of Silver	•			
	and Silver Oxide Films and Patterned	5	44/40/0000	60027 447 116	0247 447 000
10/716,838	Films	Ruan, et al.	11/18/2003	60937-147-US	8317-147-999
40/400 070	Semiconductor Process Residue	Lee, et al.	06/06/2002	60937-149-US	8317-149-999
10/162,679	Removal Composition and Process System and Method for Cleaning	Lee, et al.	00/00/2002	00937-149-03	0317-149-999
H.	Workpieces Using Supercritical				
60/469,826	Carbon Dioxide	Fury, et al.	05/13/2003	60937-150-PR	8317-150-888
00/409,020	Carbon bloxide	i dry, et al.	00/10/2000	00007 100 1 10	0011 100 000
	Abrasive-Free Chemical Mechanical				
	Polishing Composition and Polishing				
10/689,043	Process Containing Same	Yao, et al.	10/21/2003	60937-151-US	8317-151-999
10/000,040	T 100000 COMMINING COMM	100,010			
10/689,042	Wet Etch of Titanium-Tungsten Film	Patel, et al.	10/21/2003	60937-152-US	8317-152-999
,		•			
	Method of Depositing Nanostructured		r		
10/261,197	Films with Embedded Nanopores	Svendsen, et al.	09/30/2002	60937-153-US	8317-153-999
	Hydrothermal Treatment of				
10/280,270	Nanostructured Films	Mukherjee, et al.	10/23/2002	60937-167-US	8317-167-999
10/257,469	Inhibition of Titanium Corrosion	Daviot, et al.	10/11/2002	60937-168-US	8317-168-999
	Chemical Mechanical Polishing				
10/401,405	Composition andProcess	Small, et al.	03/27/2003	60937-171-US	8317-171-999
	Aqueous Phosphoric Acid				
	Compositions for Cleaning				
10/688,900	Semiconductor Devices_	Daviot, et al.	10/21/2003	60937-172-US	8317-172-999
	Load Lock System for Supercritical		00/40/0000	00007.475.110	0047.475.000
10/465,906	Fluid Cleaning	Fury, et al.	06/18/2003	60937-175-US	8317-175-999
	Automated Dense Phase Fluid	5	00/40/0000	00007 476 116	9247 476 000
10/465,905	Cleaning System	Fury, et al.	06/18/2003	60937-176-US	8317-176-999
	Residue Removers for				
CO/455 420	Electrohydrodynamic Cleaning of	Robert J. Small	03/18/2003	60937-178-PR	8317-178-888
60/455,439	Semiconductors	Robert J. Siriali	03/10/2003	00937-170-11	0317-170-000
	Free Radical-Forming Activator				
	Attached to Solid and Used to	044 -4-1	00/44/0000	C0027 470 LIC	9247 470 000
10/361,822	Enhance CMP Formulations	Scott, et al.	02/11/2003	60937-179-US	8317-179-999
40/077 500	Titanium Carboxylate Films for Use in		02/26/2003	60937-182-US	8317-182-999
10/377,533	Semiconductor Processing Method of Making Barrier Layers	Hill, et al. Maloney, et al.	05/20/2003	60937-182-US	8317-183-999
10/422,860	Remover Formulation Containing	Maioriey, et al.	03/20/2003	00337-103-00	0017-100-333
	Fluoride for Use During				
60/463,739	Semiconductor Manufacturing	Hirasawa, et al.	04/18/2003	60937-185-PR	8317-185-888
00/403,739	Cleaning Composition for Removing	i inadarra, ot an	0 17 10/2000	3333. 733 . 13	35
	Resists and Manufacturing Method of				
60/464,125	Semiconductor Devices	Hirasawa, et al.	04/21/2003	60937-186-PR	8317-186-888
50/707,120	Deposition of Permanent Polymer				
	L Denosition of Lemignem Loring				

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A TO THE RESIDENCE ACCOUNT	Market and the second of the s	CONTRACTOR NOTES		New Attorney	Carrie Marian
	Title	Inventor(s).		Docket No.	Docket No.
App #	A STATE OF CASE ASSESSMENT OF THE STATE OF T	CITIVE III (S)	ADate	E DOCKELINO.	SOUCKETINO.
40/440 050	Seimconductor Process Residue	Wai Mun Lee	05/20/2003	60937-189-US	8317-189-999
10/442,858	Removal Composition and Process Cleaning Compositions and Method of	VVai Wull Lee	03/20/2003	00937-109-00	0017-103-333
10/620 200	Use Thereof	Wai Mun Lee	07/30/2003	60937-194-US	8317-194-999
10/630,300	Compositions and Methods for	VVai Muli Lee	01130/2000	00307 134 00	0017 104 000
-	Rapidly Removing Overfilled				·
60/518,337	Substrates	Chelle, et al.	11/10/2003	60937-200-PR	8317-200-888
00/310,337	CMP Method for Copper, Tungsten,	Oriono, or al.	1111012000	00007 200 77	
	Titanium, Polysilicon, and Other			,	
	Substrates Using Organosulfonic		·		
10/690,623	Acids as Oxidizers	Carter, et al.	10/23/2003	60937-202-US	8317-202-999
10/090,023	PeriodicAcid Compositions for				
	Polishing Nobel Metal/High K				
60/494,954	Substrates	Robert J. Small	08/14/2003	60937-203-PR	8317-203-888
30/104,004	Cerium Oxide Abrasives for Chemical				
60/509,920	Mechanical Polishing	Robert J. Small	10/10/2003	60937-204-PR	8317-204-888
00,000,000		•			
!	Chemical Mechanical Polishing				
	Slurries and Cleaners Containing	•			
60/516,736	Salicyclic Acid as a Corrosion Inhibitor	Carter, et al.	11/04/2003	60937-206-PR	8317-206-888
	Periodic Acid Compositions for			,	
60/494,955	Polishing Ruthenium Substrates	Robert J. Small	08/14/2003	60937-207-PR	8317-207-888
	Chemical Mechanical Polishing				
10/683,730	Compositions and Process	Small, et al.	10/10/2003	60937-211-US	8317-211-999
	Alumia Abrasive for Chemical				
60/514,020	Mechanical Polishing	Philippe H. Chelle	10/27/1999	60937-213-PR	8317-213-888
	Chemical Mechanical Polishing				. 1
	Slurries and Cleaners Containing			00007.044.00	0047.044.000
60/502,951	Salicyclic Acid as a Corrosion Inhibitor	Tamilmani, et al.	09/16/2003	60937-214-PR	8317-214-888
	Compositions for Chemical		1		
	Mechanical Planarization of Tantalum	011 -4 -1		60937-215-US	8317-215-999
10/665,417	and Tantalum Nitride	Small, et al.	09/22/2003	00937-213-03	0317-210-999
00/500 407	Alumina Abrasive for Chemical	Chelle, et al.	12/02/2003	60937-216-PR	8317-216-888
60/526,107	Mechanical Polishing	Chene, et al.	12/02/2003	00937-210-110	0317-210-000
60/509,922	Particulate or Particle-Bound Chelating Agents	Small, et al.	10/10/2003	60937-217-PR	8317-217-888
60/309,922	Particulate or Particle-Bound	Oman, et al.	10/10/2000	00007 217 110	0011 211 000
10/690,626	Chelating Agents	Small, et al.	10/23/2003	60937-217-US	8317-217-999
10/030,020	Chemical Mechanical Polishing of STI				
	Features on Semiconductors: Water				
60/533,054	Polishing with Ceria Slurries	Yu, et al.	12/30/2003	60937-223-PR	8317-223-888
1	J				
1	Removal of Post Etch Residues and				
	Copper Contamination From Low-K				
	Dielectrics Using Superciritcal CO2				
60/511,949	with Diketone Additives	Jerome Daviot	10/14/2003	60937-225-PR	8317-225-888
,	Method and Apparatus for Substrate				
10/694,999	Pre-Treatment	Lee, et al.	10/29/2003	60937-226-US	8317-226-999

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App.#2	Title	Inventor(s).	Filing Däte	New Attorney Docket No.	Former Attorney Docket No. 3
60/515,450	Method of Chemically Mechanically Polishing Substrates	Brandon S. Scott	10/30/2003	60937-228-PR	8317-228-888